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(54) Title: METHODS OF FORMING THROUGH WAFER INTERCONNECTS IN SEMICONDUCTOR STRUCTURES USING SACRIFICIAL MATERIAL, AND SEMICONDUCTOR STRUCTURES FORMED BY SUCH METHODS

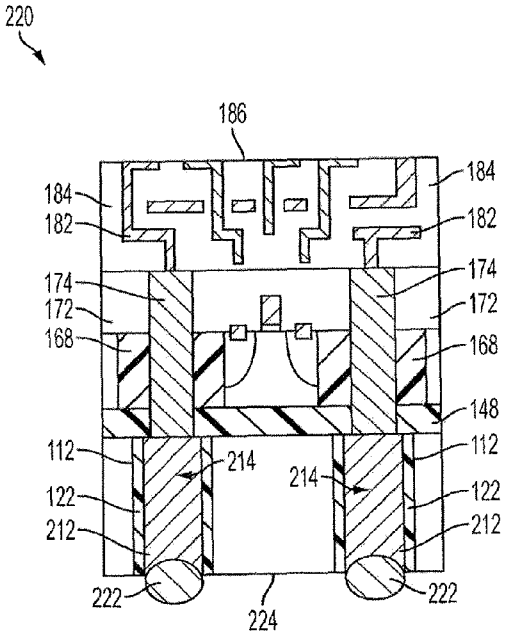


FIG. 13

(57) Abstract: Methods of fabricating semiconductor structures include providing a sacrificial (132) material within a via recess (112), forming a first portion (174) of a through wafer interconnect in the semiconductor structure, and replacing the sacrificial material with conductive material to form a second portion (212) of the through wafer interconnect. Semiconductor structures are formed by such methods. For example, a semiconductor structure may include a sacrificial material within a via recess, and a first portion of a through wafer interconnect that is aligned with the via recess. Semiconductor structures include through wafer interconnects comprising two or more portions having a boundary therebetween.

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